



STC03DE220HV

Hybrid emitter switched bipolar transistor
ESBT[®] 2200 V - 3 A - 0.33 Ω

Features

| $V_{CS(ON)}$ | I_C | $R_{CS(ON)}$ |
|--------------|-------|--------------|
| 1 V | 3 A | 0.33 Ω |

- Low equivalent on-resistance
- Very fast switching, up to 150 kHz
- Very low C_{ISS} driven by $R_G = 4.7 \Omega$

Application

- Aux SMPS for 3-phase mains

Description

The STC03DE220HV is manufactured using a hybrid structure, with dedicated high voltage bipolar and low voltage MOSFET technology, aimed at providing the best performance in an ESBT topology.

The STC03DE220HV is designed for use in an aux. flyback SMPS for any 3-phase application.

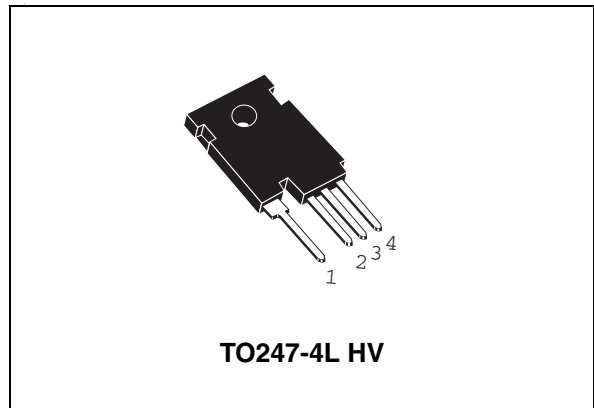


Figure 1. Internal schematic diagrams

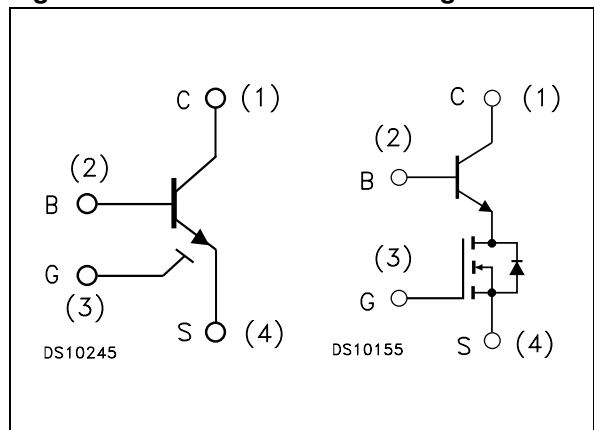


Table 1. Device summary

| Order code | Marking | Package | Packaging |
|--------------|------------|-------------|-----------|
| STC03DE220HV | C03DE220HV | TO247-4L HV | Tube |

1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|--------------|--|------------|------|
| $V_{CS(SS)}$ | Collector-source voltage ($V_{BS} = V_{GS} = 0$) | 2200 | V |
| $V_{BS(OS)}$ | Base-source voltage ($I_C = 0, V_{GS} = 0$) | 30 | V |
| $V_{SB(OS)}$ | Source-base voltage ($I_C = 0, V_{GS} = 0$) | 9 | V |
| V_{GS} | Gate-source voltage | ± 20 | V |
| I_C | Collector current | 3 | A |
| I_{CM} | Collector peak current ($t_P < 5$ ms) | 6 | A |
| I_B | Base current | 3 | A |
| I_{BM} | Base peak current ($t_P < 1$ ms) | 6 | A |
| P_{tot} | Total dissipation at $T_c \leq 25$ °C | 166 | W |
| T_{stg} | Storage temperature | -40 to 150 | °C |
| T_J | Max. operating junction temperature | 125 | °C |

Table 3. Thermal data

| Symbol | Parameter | Value | Unit |
|------------|----------------------------------|-------|------|
| R_{thJC} | Thermal resistance junction-case | 0.6 | °C/W |

2 Electrical characteristics

($T_{\text{case}} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.)

Table 4. Electrical characteristics

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|----------------------------------|---|--|------|-------------|------|---------------|
| $I_{\text{CS(SS)}}$ | Collector cut-off current ($V_{\text{BS}} = V_{\text{GS}} = 0$) | $V_{\text{CS}} = 2200\text{ V}$ | | | 100 | μA |
| $I_{\text{BS(OS)}}$ | Base cut-off current ($I_{\text{C}} = 0, V_{\text{GS}} = 0$) | $V_{\text{BS}} = 30\text{ V}$ | | | 10 | μA |
| $I_{\text{SB(OS)}}$ | Source cut-off current ($I_{\text{C}} = 0, V_{\text{GS}} = 0$) | $V_{\text{SB}} = 9\text{ V}$ | | | 100 | μA |
| $I_{\text{GS(OS)}}$ | Gate-source leakage current ($V_{\text{BS}} = 0$) | $V_{\text{GS}} = \pm 20\text{ V}$ | | | 500 | nA |
| $V_{\text{CS(ON)}}$ | Collector-source ON voltage | $V_{\text{GS}} = 10\text{ V } I_{\text{C}} = 1.5\text{ A } I_{\text{B}} = 0.15\text{ A}$ $V_{\text{GS}} = 10\text{ V } I_{\text{C}} = 3\text{ A } I_{\text{B}} = 0.6\text{ A}$ | | 0.2 0.25 | | V V |
| h_{FE} | DC current gain | $V_{\text{CS}} = 1\text{ V } V_{\text{GS}} = 10\text{ V } I_{\text{C}} = 1.5\text{ A}$ $V_{\text{CS}} = 1\text{ V } V_{\text{GS}} = 10\text{ V } I_{\text{C}} = 3\text{ A}$ | | 15 10 | | |
| $V_{\text{BS(ON)}}$ | Base-source ON voltage | $V_{\text{GS}} = 10\text{ V } I_{\text{C}} = 1.5\text{ A } I_{\text{B}} = 0.15\text{ A}$ $V_{\text{GS}} = 10\text{ V } I_{\text{C}} = 3\text{ A } I_{\text{B}} = 0.6\text{ A}$ | | 0.82 1 | | V V |
| $V_{\text{GS(th)}}$ | Gate threshold voltage | $V_{\text{BS}} = V_{\text{GS}} \quad I_{\text{B}} = 250\text{ }\mu\text{A}$ | 1.5 | 2.2 | 3 | V |
| C_{iss} | Input capacitance ($V_{\text{GS}} = V_{\text{CB}} = 0$) | $V_{\text{CS}} = 25\text{ V} \quad f = 1\text{ MHz}$ | | 750 | | pF |
| $Q_{\text{GS(tot)}}$ | Gate-source charge ($V_{\text{CB}} = 0$) | $V_{\text{CS}} = 15\text{ V} \quad V_{\text{GS}} = 10\text{ V}$ $I_{\text{C}} = 1.8\text{ A}$ | | 12.5 | | nC |
| t_{s} t_{f} | Inductive load Storage time Fall time | $V_{\text{GS}} = 10\text{ V} \quad R_{\text{G}} = 47\text{ }\Omega$ $V_{\text{Clamp}} = 1760\text{ V} \quad t_{\text{p}} = 4\text{ }\mu\text{s}$ $I_{\text{C}} = 1.5\text{ A} \quad I_{\text{B}} = 0.3\text{ A}$ | | 1040 20 | | ns ns |
| $V_{\text{CS(dyn)}}$ | Collector-source dynamic voltage (0.5 μs) | $V_{\text{CC}} = V_{\text{Clamp}} = 400\text{ V}$ $V_{\text{GS}} = 10\text{ V} \quad I_{\text{C}} = 1.5\text{ A}$ $I_{\text{B}} = 0.3\text{ A} \quad R_{\text{G}} = 47\text{ }\Omega$ $t_{\text{peak}} = 500\text{ ns} \quad I_{\text{Bpeak}} = 3\text{ A}$ | | 7.6 | | V |
| $V_{\text{CS(dyn)}}$ | Collector-source dynamic voltage (1 μs) | $V_{\text{CC}} = V_{\text{Clamp}} = 400\text{ V}$ $V_{\text{GS}} = 10\text{ V} \quad I_{\text{C}} = 1.5\text{ A}$ $I_{\text{B}} = 0.3\text{ A} \quad R_{\text{G}} = 47\text{ }\Omega$ $t_{\text{peak}} = 500\text{ ns} \quad I_{\text{Bpeak}} = 3\text{ A}$ | | 5.8 | | V |
| V_{CSW} | Maximum collector-source voltage at turn-off without snubber | $R_{\text{G}} = 47\text{ }\Omega \quad h_{\text{FE}} = 5 \quad I_{\text{C}} = 3\text{ A}$ | 2200 | | | V |

2.1 Electrical characteristics (curves)

Figure 2. DC current gain

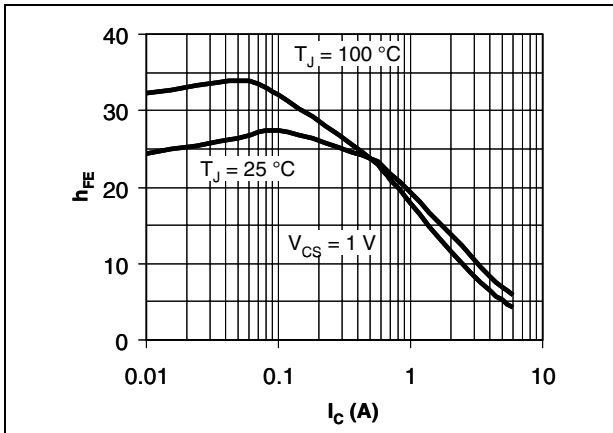


Figure 3. Base-source ON voltage

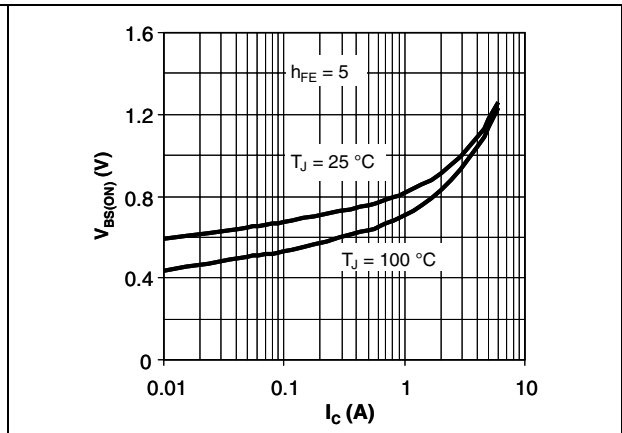


Figure 4. Collector-source ON voltage

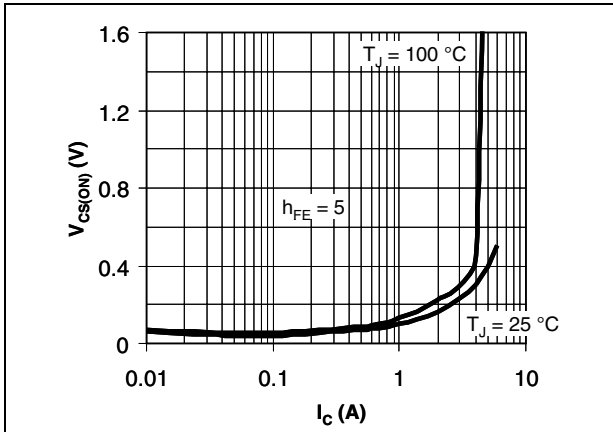


Figure 5. Collector-source dynamic voltage

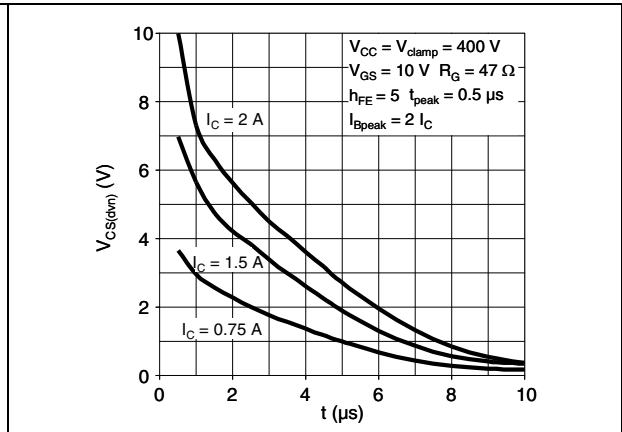


Figure 6. Inductive load switching off ($T_C = 25^\circ\text{C}$)

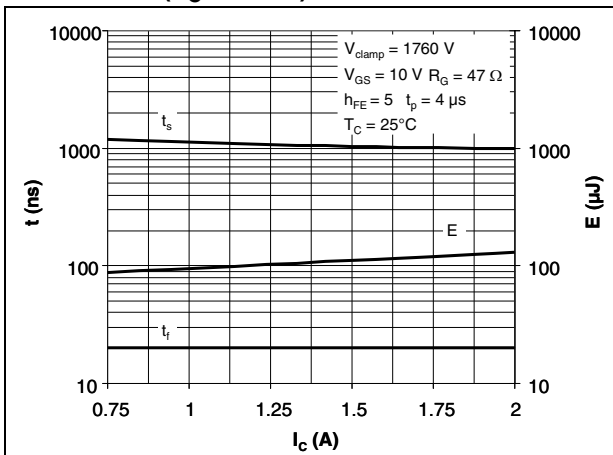


Figure 7. Inductive load switching off ($T_C = 100^\circ\text{C}$)

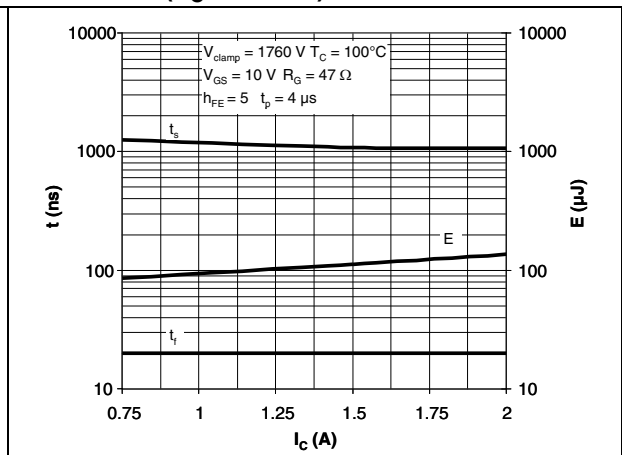
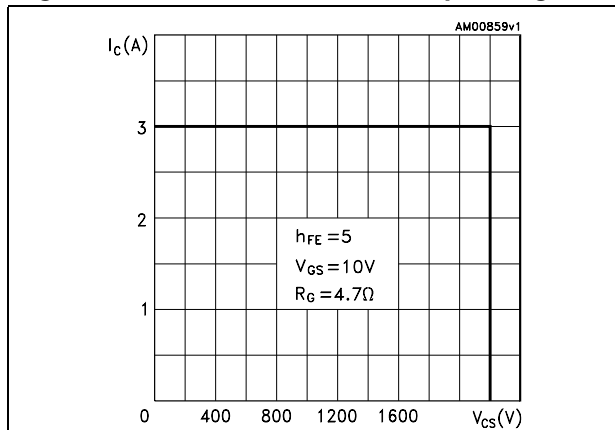


Figure 8. Reverse biased safe operating area



3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

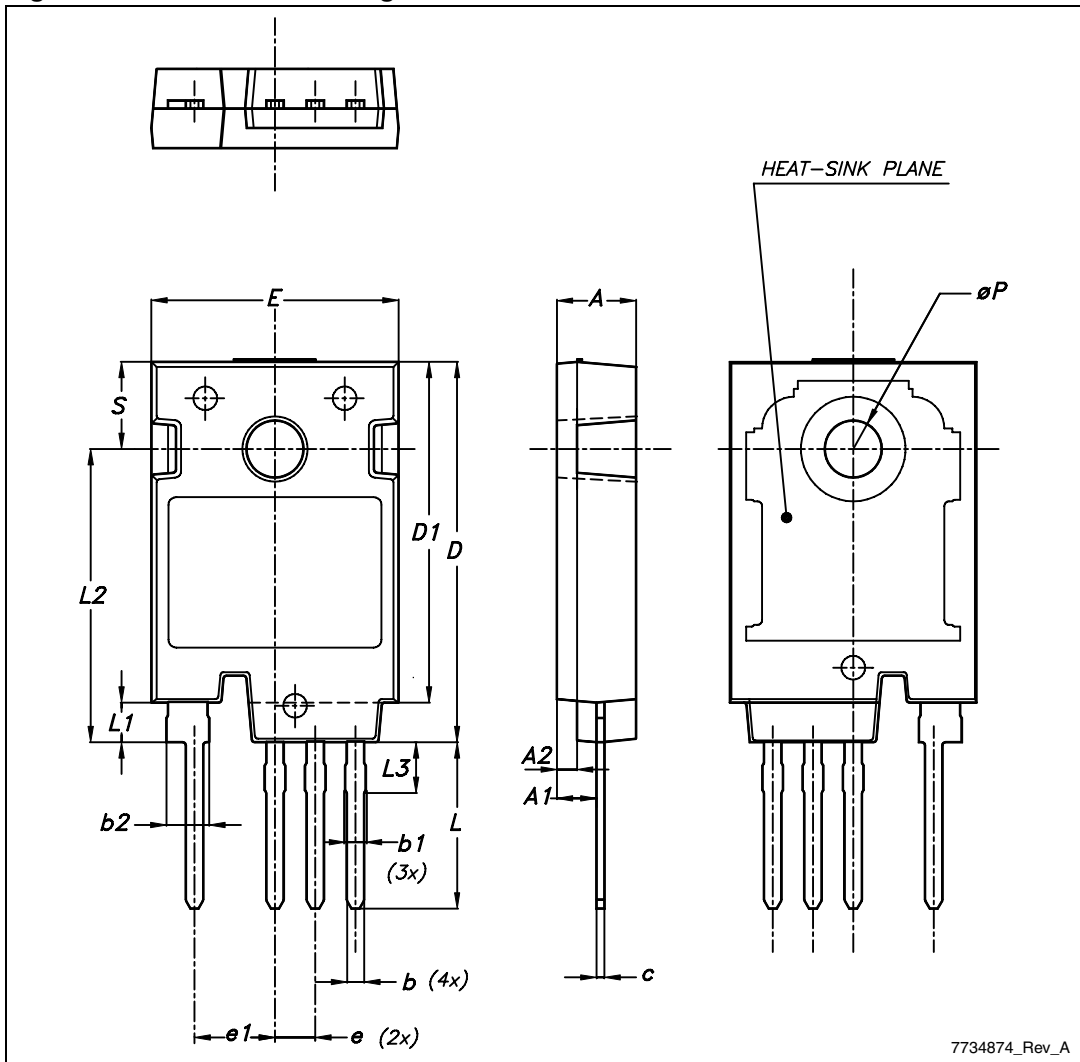
Table 5. TO-247-4L mechanical data

| Dim. | mm. | | | Notes |
|------|-------|-------|-------|-------|
| | Min. | Typ. | Max. | |
| A | 4.85 | | 5.15 | |
| A1 | 2.20 | 2.50 | 2.60 | |
| A2 | | | 1.27 | |
| b | 0.95 | 1.10 | 1.30 | |
| b1 | 1.10 | | 1.50 | |
| b2 | 2.50 | | 2.90 | |
| c | 0.40 | | 0.80 | |
| D | 23.85 | 24 | 24.15 | 5 |
| D1 | | 21.50 | | |
| E | 15.45 | 15.60 | 15.75 | |
| e | | 2.54 | | |
| e1 | | 5.08 | | |
| L | 10.20 | | 10.80 | |
| L1 | 2.20 | 2.50 | 2.80 | |
| L2 | | 18.50 | | |
| L3 | | 3 | | |
| ØP | 3.55 | | 3.65 | 4 |
| S | | 5.50 | | |

General package performance

1. The lead size is comprehensive of the thickness of the leads finishing material.
2. The leads must be covered with soldered alloy up to 1,3 mm from the plastic package.
3. Package outline exclusive of any mold flash dimensions and metal burrs.
4. Resin thickness around the mounting hole must not be less than 0,9 mm.
5. "D" dimension plus gate protrusion, must not exceed 24,5 mm.
6. Package backside planarity: the level of the resin surrounding the heatsink must not be higher than 30 microns versus the heatsink plan.
7. Torque force (through hole package): recommended: 0,55 Nm // maximum: 1 Nm.
8. The maximum bent leads allowed, in any direction, is: # 2° if the devices are packed in tube.
9. Package weight: 4,78 g / unit (typ.).

Figure 9. TO-247-4L drawing



4 Revision history

Table 6. Document revision history

| Date | Revision | Changes |
|-------------|----------|---|
| 27-Nov-2006 | 1 | First release. |
| 19-May-2008 | 2 | Document status promoted from preliminary data to datasheet. |
| 10-Jun-2009 | 3 | Added Section 2.1: Electrical characteristics (curves) on page 4. |
| 25-Jan-2012 | 4 | Mechanical data updated |

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